

## NPN+PNP Dual Transistors

### Features

- Epitaxial planar die construction
- Power Dissipation of 200mW
- Two internal isolated NPN/PNP transistors in one package
- RoHS Compliant

### Applications

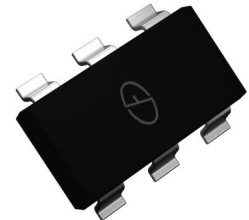
- General purpose small signal amplifier

### Mechanical Data

- Package: SOT-363
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020



**RoHS**  
COMPLIANT



Marking: .7P

SOT-363

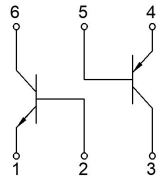


### Pin definition

### Equivalent circuit



2.5: Base  
1.4: Emitter  
3.6: Collector



### Maximum Ratings & Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value		Unit
		TR1	TR2	
Collector-Base Voltage	V <sub>CB0</sub>	50	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	45	-45	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	-5	V
Collector Current Continuous	I <sub>c</sub>	100	-100	mA
Collector Power Dissipation	P <sub>D</sub>	200		mW
Operating Junction temperature	T <sub>J</sub>	-55 to +150		°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150		°C

**TR1 NPN Electrical Specifications** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

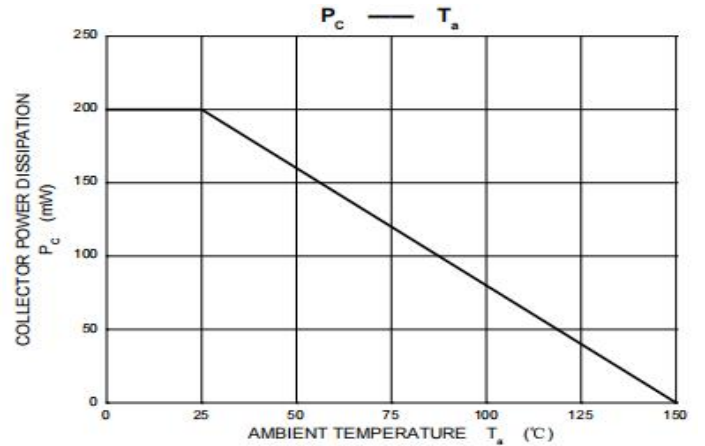
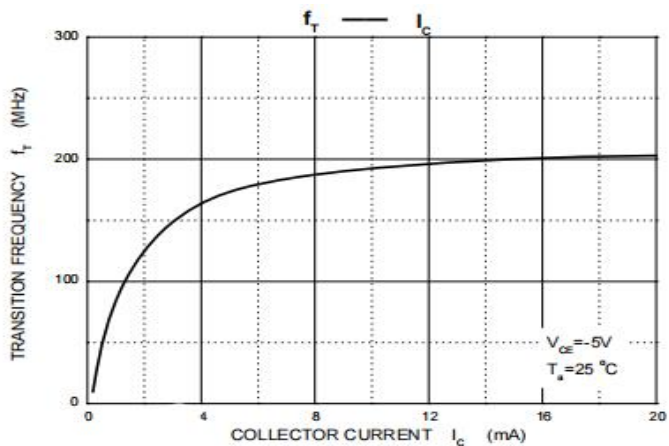
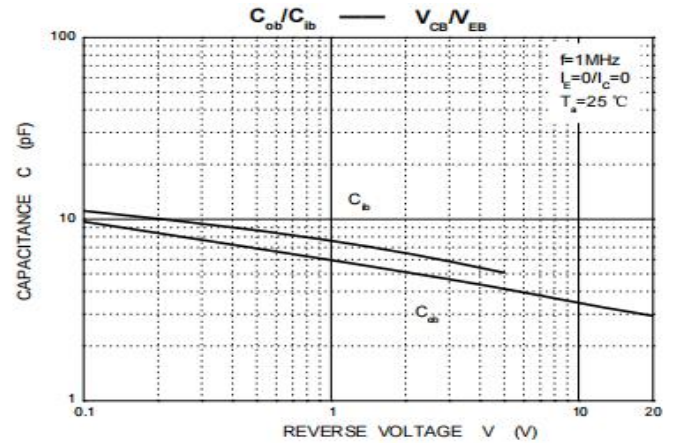
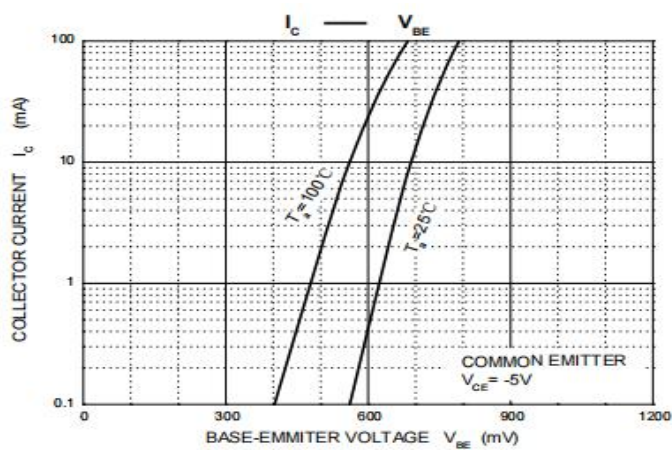
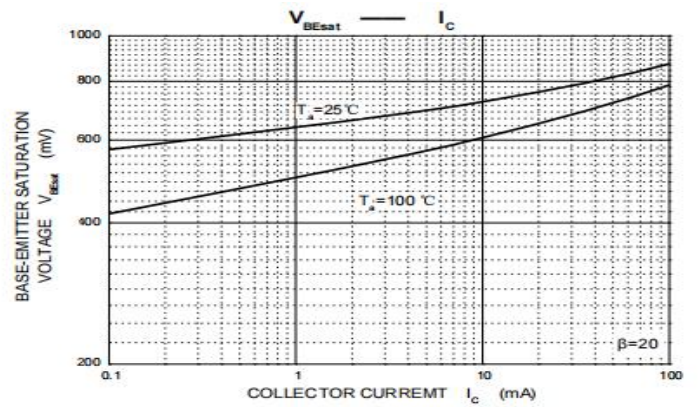
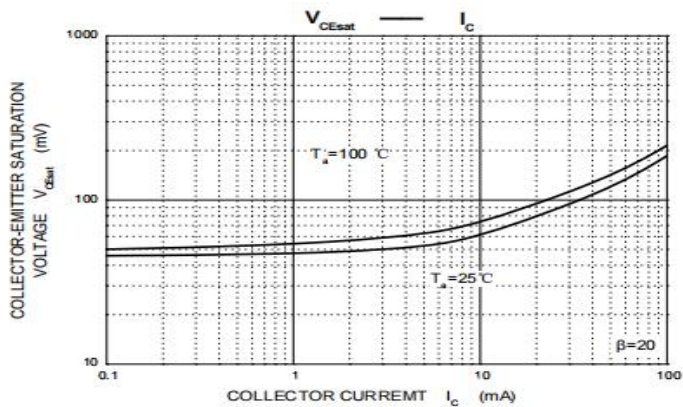
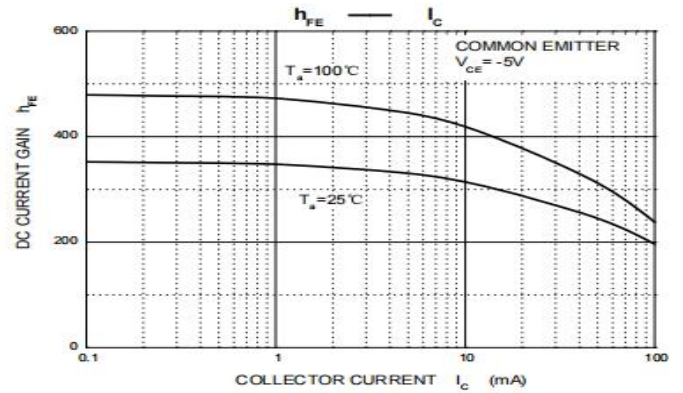
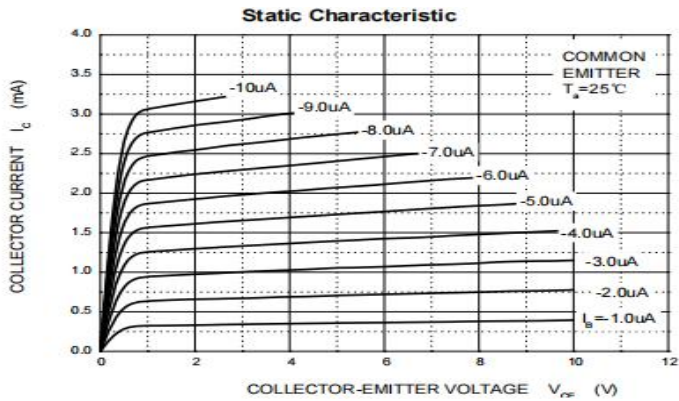
Parameter	Symbol	Test Conditions	Limit			Unit
			Min	Typ	Max	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	50			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	45			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1\mu\text{A}, I_C = 0$	6			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 30\text{V}, I_E = 0$			15	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$			15	nA
DC Current Gain	$h_{FE}$	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$	200		450	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$			0.25	V
		$I_C = 100\text{mA}, I_B = 5\text{mA}$			0.60	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$		0.7		V
		$I_C = 100\text{mA}, I_B = 5\text{mA}$		0.9		V
Base-Emitter Voltage	$V_{BE(ON)}$	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$	0.58		0.70	V
		$V_{CE} = 5\text{V}, I_C = 10\text{mA}$			0.72	V
Transition frequency	$f_T$	$V_{CE}=5\text{V}, I_C=10\text{mA}$ $f=100\text{MHz}$	100			MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}$			6.0	pF
Noise Figure	$N_F$	$V_{CE} = 5\text{V}, f=1.0\text{KHz}$ $I_C=200\text{mA}, R_G = 2\text{k}\Omega$			10	dB

**TR2 PNP Electrical Specifications** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Parameter	Symbol	Test Conditions	Limit			Unit
			Min	Typ	Max	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-50			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-45			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1\mu\text{A}, I_C = 0$	-5			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -30\text{V}, I_E = 0$			-15	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$			-15	nA
DC Current Gain	$h_{FE}$	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	220		475	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$			-0.3	V
		$I_C = -100\text{mA}, I_B = -5\text{mA}$			-0.65	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$		-0.70		V
		$I_C = -100\text{mA}, I_B = -5\text{mA}$			-0.95	V
Base-Emitter Voltage	$V_{BE(ON)}$	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	-0.6		-0.75	V
		$V_{CE} = -5\text{V}, I_C = -10\text{mA}$			-0.82	V
Transition frequency	$f_T$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$ $f=100\text{MHz}$	100			MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}$			4.5	pF
Noise Figure	$N_F$	$V_{CE} = -5\text{V}, f=1.0\text{KHz}$ $I_C = -200\text{mA}, R_G = -2\text{k}\Omega$			10	dB

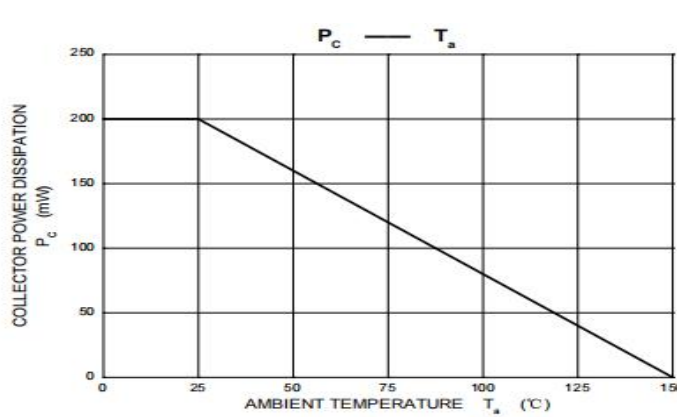
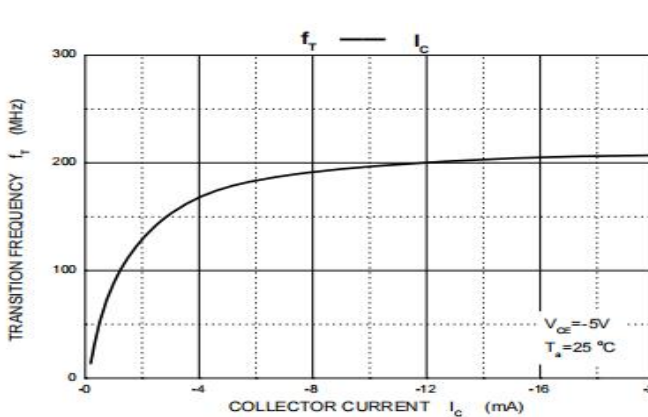
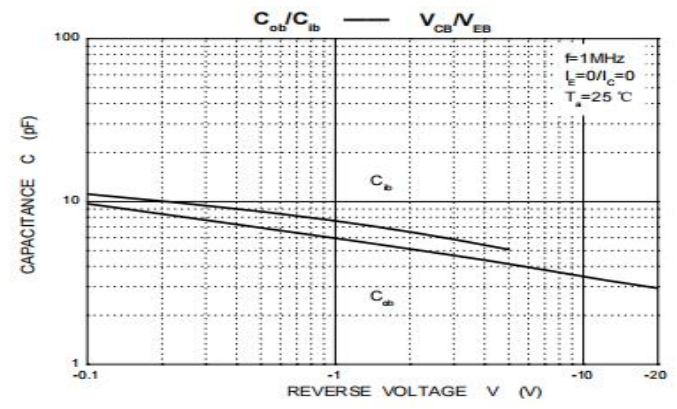
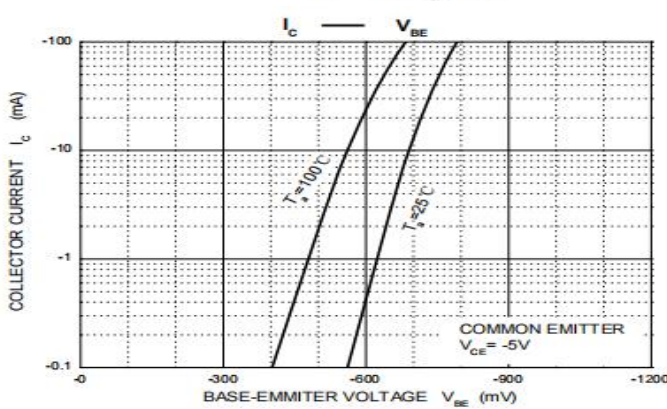
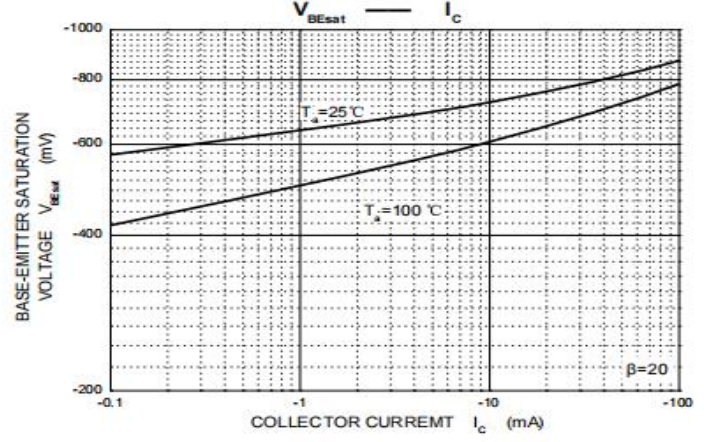
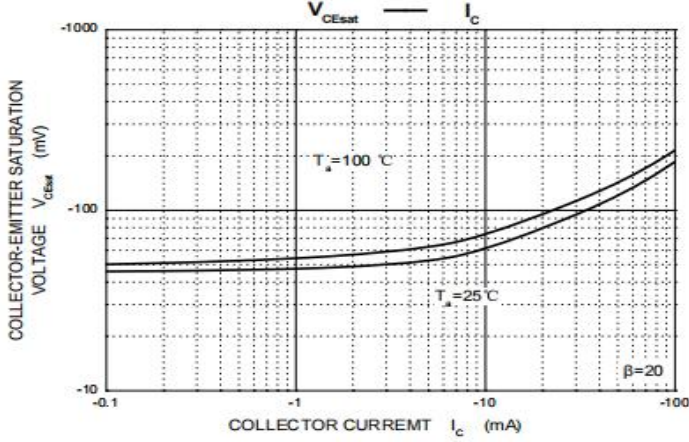
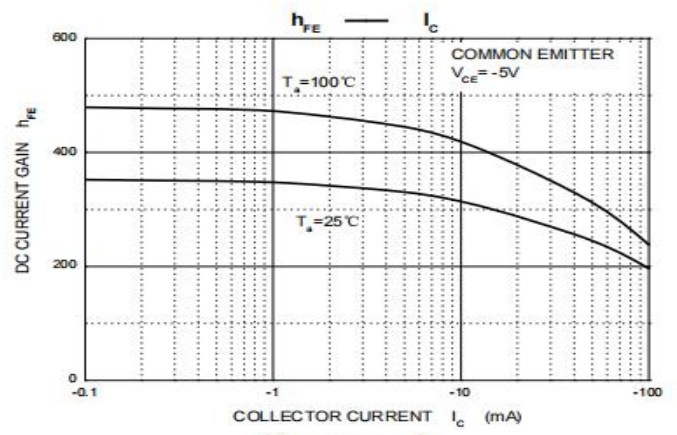
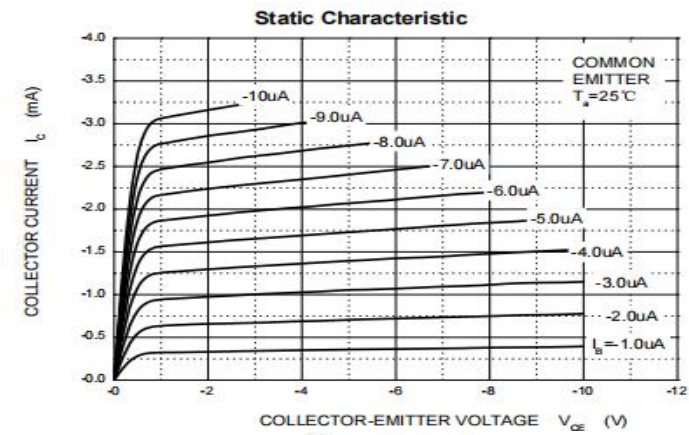
## Ratings and Characteristics Curves

( $T_A = 25^\circ\text{C}$  unless otherwise noted)



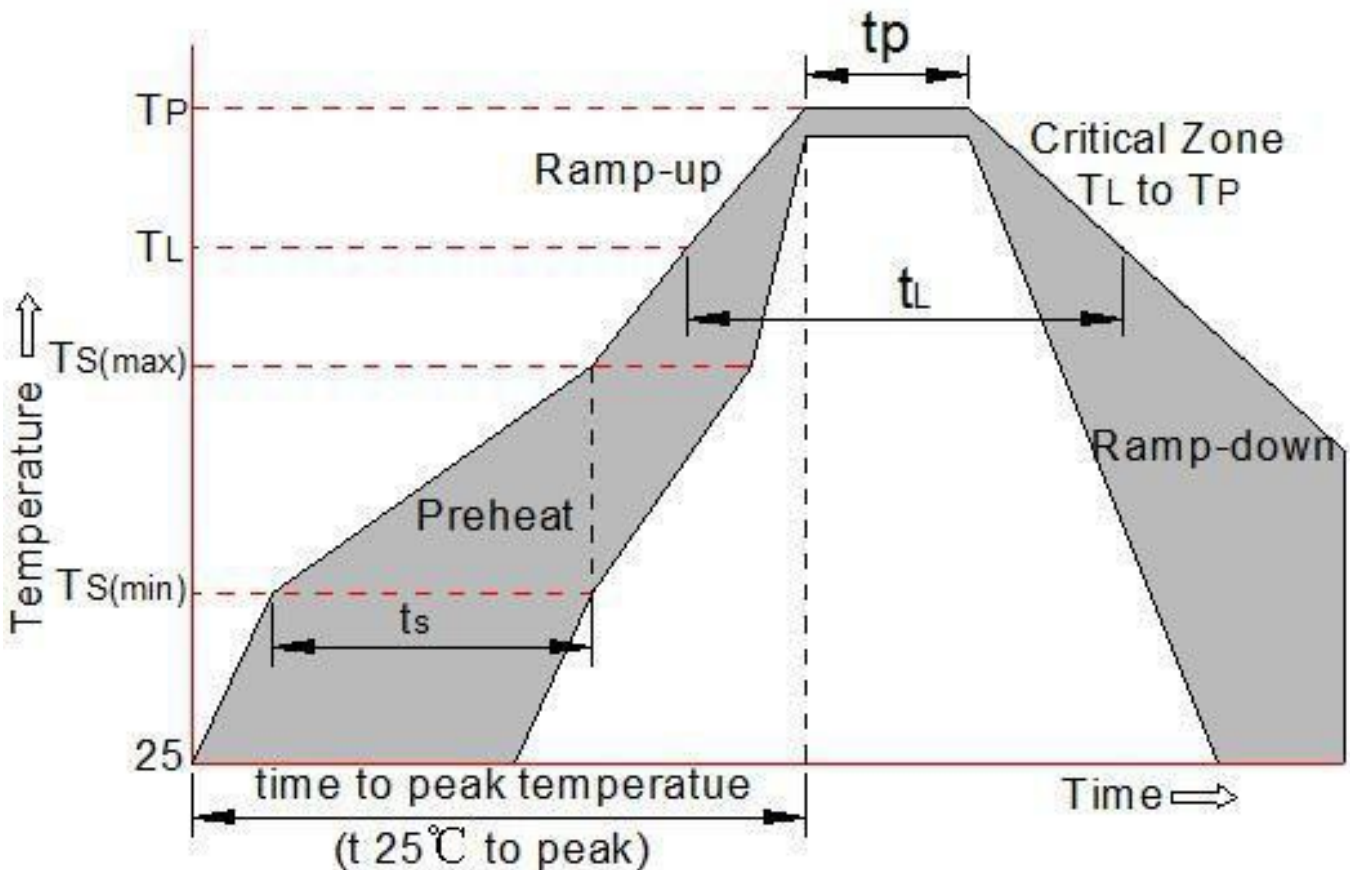
## Ratings and Characteristics Curves

( $T_A = 25^\circ\text{C}$  unless otherwise noted)



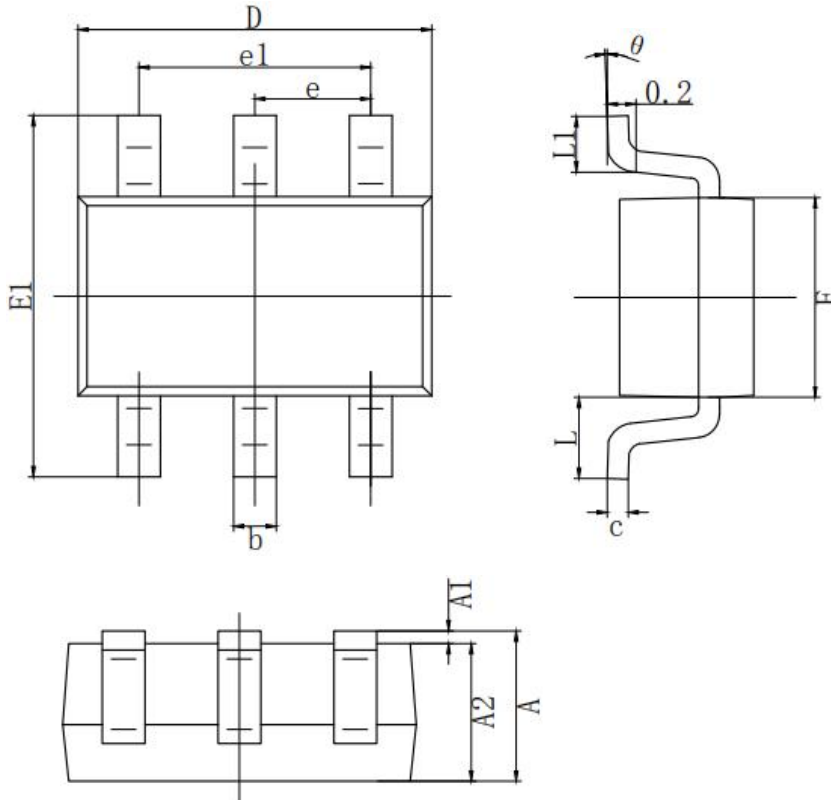
## Soldering Parameters

Reflow Condition		Pb -Free assembly (see as bellow)
Pre Heat	-Temperature Min ( $T_{s(min)}$ )	+150 °C
	-Temperature Max( $T_{s(max)}$ )	+200 °C
	-Time (Min to Max) ( $t_s$ )	60 -180 secs.
Average ramp up rate (Liquid us Temp ( $T_L$ ) to peak)		3 °C /sec. Max
$T_{s(max)}$ $T_L$ - Ramp -up Rate		3 °C /sec. Max
Reflow	-Temperature( $T_L$ ) (Liquid us)	+217 °C
	-Temperature( $t_L$ )	60 -150 secs.
Peak Temp ( $T_p$ )		+260(+0/ -5) °C
Time within 5 °C of actual Peak Temp ( $t_p$ )		30 secs. Max
Ramp -down Rate		6 °C /sec. Max
Time 25 °C to Peak Temp ( $T_p$ )		8 min. Max
Do not exceed		+260 °C



## Package Outline Dimensions

in inches (millimeters)



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
θ	0°	8°

## Revision History

Document Version	Date of release	Description of changes
Rev.A	2017.06.13	First issue

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